## Slotted Optical Switch OPB660N, OPB660T

## $\top_{\top}$ Electronics

## Features:

- Non-contact switching
- Printed circuit board mounting
- Enhanced signal to noise ratio
- Gap $0.125^{\prime \prime}(3.18 \mathrm{~mm})$ wide and $0.345^{\prime \prime}$ ( 8.76 mm ) deep slot
- Emitter Aperture $0.05^{\prime \prime} \times 0.06^{\prime \prime}$ ( $1.27 \mathrm{~mm} \times 1.52 \mathrm{~mm}$ ),
- Sensor Aperture $0.01^{\prime \prime} \times 0.06^{\prime \prime}(0.25 \mathrm{~mm} \times 1.52 \mathrm{~mm})$



## Description:

Each OPB660 slotted optical switch consists of an infrared emitting diode and a NPN silicon phototransistor, combined with an enhanced low current roll-off that improves contrast ratio and provides immunity to background irradiance. Housings are made from an opaque grade of injection-molded plastic to minimize sensitivity to both visible and near-infrared light.

## Applications:

- Non-contact transmissive object sensor
- Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor

| Part <br> Number | LED Peak <br> Wavelength | Sensor | Slot Width $/$ <br> Depth | Aperture <br> Emitter/Sensor | Lead Length / <br> Spacing |
| :---: | :---: | :---: | :---: | :---: | :---: |
| OPB660N | 890 nm | Rbe <br> Transistor | $0.125^{\prime \prime} / 0.345^{\prime \prime}$ | $0.05^{\prime \prime} / 0.01^{\prime \prime}$ | $0.100^{\prime \prime} / 0.320^{\prime \prime}$ <br> (MIN) |
| OPB660T | 89 |  |  |  |  |



| Pin \# | LED | Pin \# | Transistor |
| :---: | :---: | :---: | :---: |
| 1 | Anode | 3 | Collector |
| 2 | Cathode | 4 | Emitter |



[^0]
## Electrical Specifications

Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted)

| Storage \& Operating Temperature Range | $-40^{\circ} \mathrm{C}$ to $+100^{\circ} \mathrm{C}$ |
| :--- | ---: |
| Lead Soldering Temperature $\left[1 / 16\right.$ inch $(1.6 \mathrm{~mm})$ from the case for 5 sec. with soldering iron ${ }^{(1)}$ | $260^{\circ} \mathrm{C}$ |

Input Diode

| Forward DC Current | 50 mA |
| :--- | ---: |
| Peak Forward Current $(1 \mu \mathrm{~s}$ pulse width, 300 pps$)$ | 1 A |
| Reverse DC Voltage | 3 V |
| Power Dissipation ${ }^{(2)}$ | 100 mW |

Output Phototransistor

| Collector-Emitter Voltage | 24 V |
| :--- | ---: |
| Collector DC Current | 30 mA |
| Power Dissipation $^{(3)}$ | 200 mW |

Electrical Characteristics ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted)

| SYMBOL | PARAMETER | MIN | TYP | MAX | UNITS | TEST CONDITIONS |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |

Input Diode

| $\mathrm{V}_{\mathrm{F}}$ | Forward Voltage | - | - | 1.6 | V | $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}$ |
| :---: | :--- | :---: | :---: | :---: | :---: | :--- |
| $\mathrm{I}_{\mathrm{R}}$ | Reverse Current | - | - | 100 | $\mu \mathrm{~A}$ | $\mathrm{~V}_{\mathrm{R}}=3 \mathrm{~V}$ |

Output Phototransistor

| $\mathrm{V}_{(\mathrm{BR}) \text { CEO }}$ | Collector-Emitter Breakdown Voltage | 24 | - | - | V | $\mathrm{I}_{\mathrm{CE}}=100 \mu \mathrm{~A}$ |
| :---: | :--- | :---: | :---: | :---: | :---: | :--- |
| $\mathrm{BV}_{\text {ECO }}$ | Emitter Reverse Breakdown Voltage | 0.4 | - | - | V | $\mathrm{I}_{\mathrm{EC}}=100 \mu \mathrm{~A}$ |
| $\mathrm{I}_{\text {CEO }}$ | Collector-Emitter Dark Current | - | - | 100 | $\mu \mathrm{~A}$ | $\mathrm{~V}_{\mathrm{CE}}=5 \mathrm{~V}$ |

## Combined

| $\mathrm{V}_{\text {SAT }}$ | Collector-Emitter Saturation Voltage | - | - | 0.4 | V | $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}, \mathrm{I}_{\mathrm{C}}=100 \mu \mathrm{~A}$, (gap unblocked) |
| :---: | :--- | :---: | :---: | :---: | :---: | :--- |
| $\mathrm{I}_{\mathrm{C}(\mathrm{ON})}$ | On-State Collector Current | 600 | - | - | $\mu \mathrm{A}$ | $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=5 \mathrm{~V}$ |

Notes:
(1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering. A maximum of 20 grams force may be applied to leads when soldering.
(2) Derate linearly $1.33 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $25^{\circ} \mathrm{C}$.
(3) Derate linearly $2.0 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $25^{\circ} \mathrm{C}$.

## Slotted Optical Switch

OPB660N, OPB660T

## $\top_{T}$ Electronics

## Performance




## X-ON Electronics

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    [ MILLIMETERS] INCHES

